N-Channel 40-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

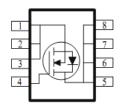
- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
40	5.5 @ V _{GS} = 10V	25		
	$7 @ V_{GS} = 4.5V$	22		









ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage	V_{DS}	40	V				
Gate-Source Voltage		V_{GS}	±20	V			
Continuous Drain Current ^a	T _A =25°C	I_	25				
Continuous Diain Current	T _A =70°C	l _D	20	Α			
Pulsed Drain Current ^b		I _{DM}	50				
Continuous Source Current (Diode Conduction) a		I _S	7.3	Α			
Dower Dissipation a	T _A =25°C	P_{D}	5	W			
Power Dissipation ^a	T _A =70°C	' D	3.2	V V			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State		65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

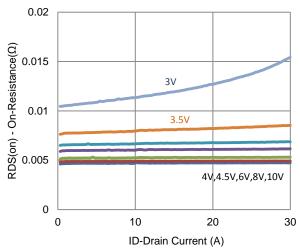
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$	1		1	uA	
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$	5		5.5	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$			7	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		23		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.65 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V},$		32			
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		12		nC	
Gate-Drain Charge	Q_gd	1D = 20 A		10			
Turn-On Delay Time	t _{d(on)}			10			
Rise Time	t _r	V_{DS} = 20 V, R_L = 1 Ω , I_D = 20 A,		13		ns	
Turn-Off Delay Time	t _{d(off)}	V_{GEN} = 10 V, R_{GEN} = 6 Ω		86			
Fall Time	t _f			24			
Input Capacitance	C _{iss}			2829			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		289		pF	
Reverse Transfer Capacitance	C_{rss}			250			

Notes

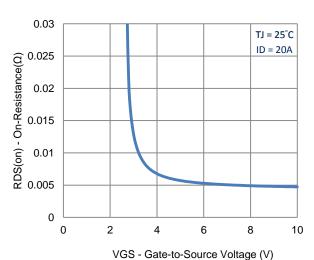
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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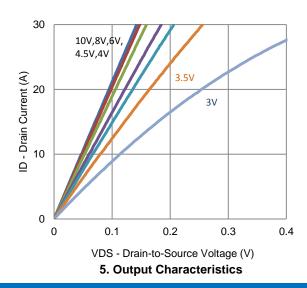
Typical Electrical Characteristics



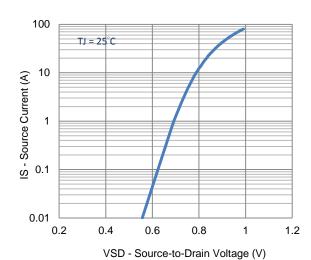
1. On-Resistance vs. Drain Current



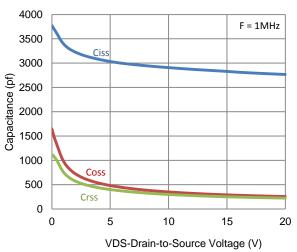
3. On-Resistance vs. Gate-to-Source Voltage



2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



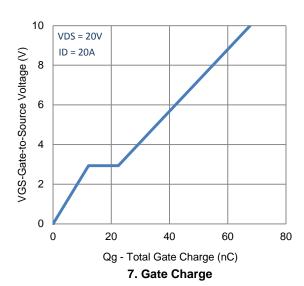
6. Capacitance

Typical Electrical Characteristics

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1.5

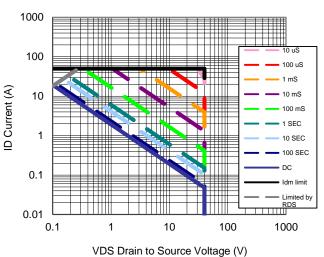
 $RDS(on) \text{ - }On\text{-}Resistance}(\Omega)$ (Normalized)

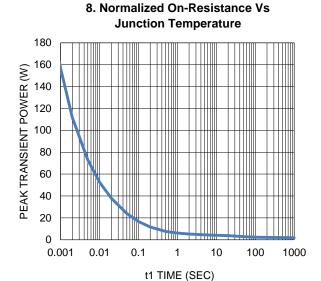


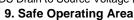
0.5 -50 -25 0 25 50 75 100 125

TJ -JunctionTemperature(°C)

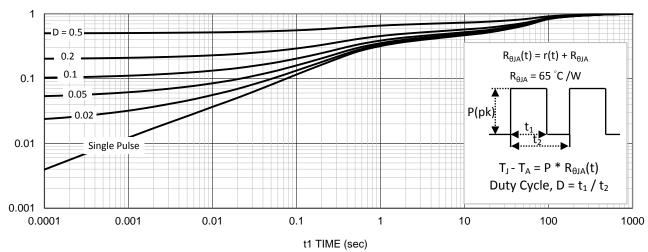
150





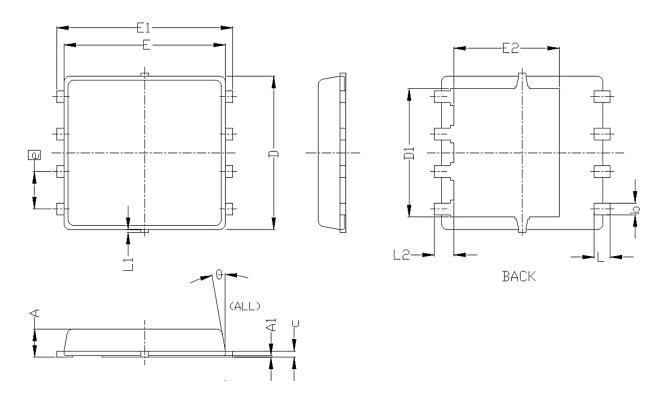


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



CAN WOLC	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0. 15	0.20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1		4. 35 BSC			0. 171 BSC		
Е	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	